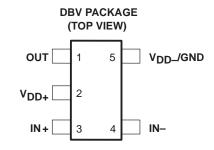
- Output Swing Includes Both Supply Rails
- Low Noise . . . 21 nV/ $\sqrt{\text{Hz}}$  Typ at f = 1 kHz
- Low Input Bias Current . . . 1 pA Typ
- Very Low Power . . . 11 μA Per Channel Typ
- Common-Mode Input Voltage Range Includes Negative Rail
- Wide Supply Voltage Range 2.7 V to 10 V
- Available in the SOT-23 Package
- Macromodel Included

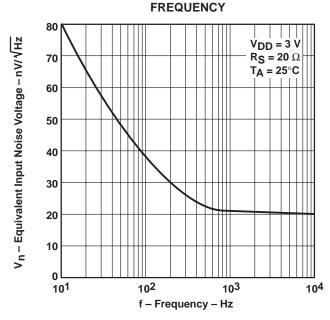
#### description

The TLV2711 is a single low-voltage operational amplifier available in the SOT-23 package. It consumes only 11  $\mu A$  (typ) of supply current and is ideal for battery-power applications. Looking at Figure 1, the TLV2711 has a 3-V noise level of 21 nV/ $\sqrt{\text{Hz}}$  at 1 kHz; five times lower than competitive SOT-23 micropower solutions. The device exhibits rail-to-rail output performance for increased dynamic range in single- or split-supply applications. The TLV2711 is fully characterized at 3 V and 5 V and is optimized for low-voltage applications.

The TLV2711, exhibiting high input impedance and low noise, is excellent for small-signal conditioning for high-impedance sources, such as piezoelectric transducers. Because of the micropower dissipation levels combined with 3-V operation, these devices work well in hand-held monitoring and remote-sensing applications. In addition, the rail-to-rail output feature with single or split supplies makes this family a great choice when interfacing with analog-to-digital converters (ADCs).



# EQUIVALENT INPUT NOISE VOLTAGE†



† For all curves where  $V_{DD} = 5$  V, all loads are referenced to 2.5 V. For all curves where  $V_{DD} = 3$  V, all loads are referenced to 1.5 V.

Figure 1. Equivalent Input Noise Voltage Versus Frequency

With a total area of 5.6mm<sup>2</sup>, the SOT-23 package only requires one-third the board space of the standard 8-pin SOIC package. This ultra-small package allows designers to place single amplifiers very close to the signal source, minimizing noise pick-up from long PCB traces.

#### **AVAILABLE OPTIONS**

	т.	Viemey AT 25°C	PACKAGED DEVICES	SYMBOL	CHIP FORM‡
	TA	V <sub>IO</sub> max AT 25°C	SOT-23 (DBV) <sup>†</sup>	STIVIBUL	(Y)
	0°C to 70°C	3 mV	TLV2711CDBV	VAJC	TI V2711Y
1	-40°C to 85°C	3 mV	TLV2711IDBV	VAJI	ILV2/III

<sup>†</sup>The DBV package available in tape and reel only.

<sup>‡</sup> Chip forms are tested at  $T_A = 25^{\circ}C$  only.



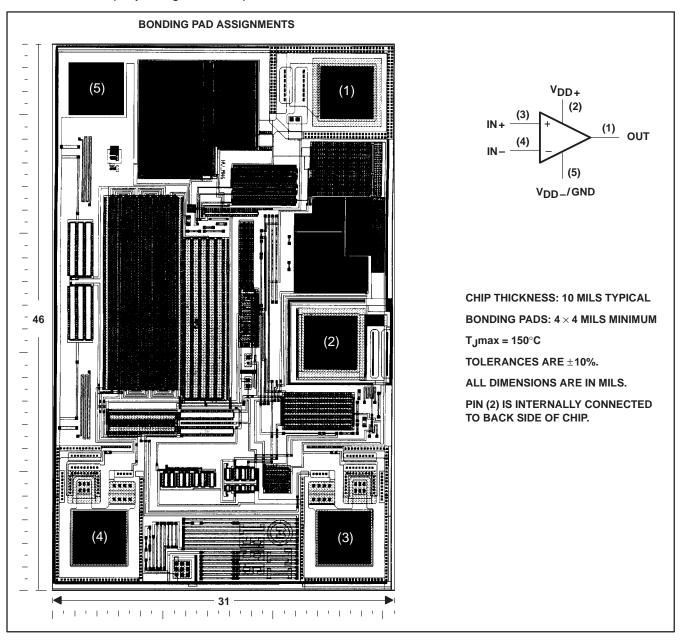
Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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TEXAS INSTRUMENTS

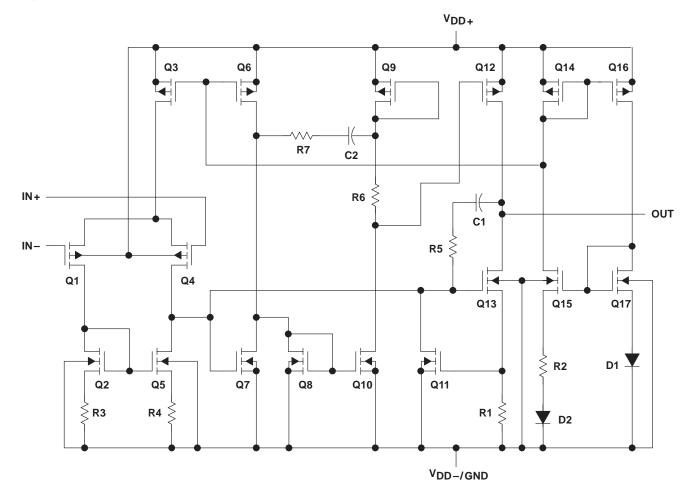
#### **TLV2711Y chip information**

This chip, when properly assembled, displays characteristics similar to the TLV2711C. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. This chip may be mounted with conductive epoxy or a gold-silicon preform.





## equivalent schematic



COMPONENT COUNT <sup>†</sup>						
Transistors	23					
Diodes	6					
Resistors	11					
Capacitors	2					

<sup>†</sup> Includes both amplifiers and all ESD, bias, and trim circuitry

## TLV2711, TLV2711Y Advanced LinCMOS™ RAIL-TO-RAIL MICROPOWER SINGLE OPERATIONAL AMPLIFIERS

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### absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage, V <sub>DD</sub> (see Note 1)	
Differential input voltage, V <sub>ID</sub> (see Note 2)	±V <sub>DD</sub>
Input voltage range, V <sub>I</sub> (any input, see Note 1)	
Input current, I <sub>I</sub> (each input)	±5 mA
Output current, I <sub>O</sub>	±50 mA
Total current into V <sub>DD+</sub>	±50 mA
Total current out of V <sub>DD</sub>	±50 mA
Duration of short-circuit current (at or below) 25°C (see Note 3)	unlimited
Continuous total power dissipation	See Dissipation Rating Table
Operating free-air temperature range, T <sub>A</sub> : TLV2711C	0°C to 70°C
TLV2711I	–40°C to 85°C
Storage temperature range, T <sub>stg</sub>	–65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds: DBV package	

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values, except differential voltages, are with respect to V<sub>DD</sub> \_.
  - 2. Differential voltages are at the noninverting input with respect to the inverting input. Excessive current flows when input is brought below V<sub>DD</sub> = 0.3 V.
  - 3. The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure that the maximum dissipation rating is not exceeded.

#### **DISSIPATION RATING TABLE**

PACKAGE	$T_{\mbox{A}} \le 25^{\circ}\mbox{C}$ Power rating	DERATING FACTOR ABOVE T <sub>A</sub> = 25°C	T <sub>A</sub> = 70°C POWER RATING	T <sub>A</sub> = 85°C POWER RATING
DBV	150 mW	1.2 mW/°C	96 mW	78 mW

#### recommended operating conditions

	TLV2711C MIN MAX		TI	UNIT	
			MIN	MAX	UNII
Supply voltage, V <sub>DD</sub> (see Note 1)	2.7	10	2.7	10	V
Input voltage range, V <sub>I</sub>	$V_{DD-}$	V <sub>DD+</sub> -1.3	V <sub>DD</sub> -	V <sub>DD+</sub> -1.3	V
Common-mode input voltage, V <sub>IC</sub>	V <sub>DD</sub> _	V <sub>DD+</sub> -1.3	V <sub>DD</sub> _	V <sub>DD+</sub> -1.3	V
Operating free-air temperature, T <sub>A</sub>	0	70	-40	85	°C

NOTE 1: All voltage values, except differential voltages, are with respect to VDD -.



# electrical characteristics at specified free-air temperature, $V_{DD}$ = 3 V (unless otherwise noted)

	DADAMETED	TEST COND	TEST CONDITIONS		Т	LV27110	C	Т	LV2711	I	
	PARAMETER	TEST COND	IIIONS	T <sub>A</sub> †	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
۷ <sub>IO</sub>	Input offset voltage					0.4	3		0.4	3	mV
αVIO	Temperature coefficient of input offset voltage			Full range		1			1		μV/°C
	Input offset voltage long-term drift (see Note 4)	$V_{DD\pm} = \pm 1.5 \text{ V},$ $V_{O} = 0,$	$V_{IC} = 0$ , RS = 50 $\Omega$	25°C		0.003			0.003		μV/mo
IIO	Input offset current			25°C		0.5	60		0.5	60	
10	input onset ourient			Full range			150			150	pА
I <sub>IB</sub>	Input bias current			25°C			60			60	PΑ
מוי	Input bias current			Full range		1	150		1	150	
\	Common-mode input	mmon-mode input	D- 50.0	25°C	0 to 2	-0.3 to 2.2		0 to 2	-0.3 to 2.2		V
VICR	voltage range	. IIVIO I < 5 mV	$R_S = 50 \Omega$	Full range	0 to 1.7			0 to 1.7			V
		I <sub>OH</sub> = -100 μA		25°C		2.94			2.94		
Vон	High-level output voltage			25°C		2.85			2.85		V
	voitage	I <sub>OH</sub> = -250 μA		Full range	2.6			2.6			
		V <sub>IC</sub> = 1.5 V,	I <sub>OL</sub> = 50 μA	25°C		15			15		
VOL	Low-level output voltage	V 4.5.V		25°C		150			150		mV
	voltage	V <sub>IC</sub> = 1.5 V,	$I_{OL} = 500 \mu\text{A}$	Full range			500			500	
	Large-signal differential voltage	I voltage $V_{IC} = 1.5 \text{ V},$	5 401 ot	25°C	3	7		3	7		
AVD			$R_L = 10 \text{ k}\Omega^{\ddagger}$	Full range	1			1			V/mV
	amplification	1 10 2 1	$R_L = 1 M\Omega^{\ddagger}$	25°C		600			600		
r <sub>i(d)</sub>	Differential input resistance			25°C		10 <sup>12</sup>			10 <sup>12</sup>		Ω
r <sub>i(c)</sub>	Common-mode input resistance			25°C		10 <sup>12</sup>			1012		Ω
c <sub>i(c)</sub>	Common-mode input capacitance	f = 10 kHz,		25°C		5			5		pF
z <sub>O</sub>	Closed-loop output impedance	f = 7 kHz,	A <sub>V</sub> = 1	25°C		200			200		Ω
CMRR	Common-mode rejection ratio	$V_{IC} = 0 \text{ to } 1.7 \text{ V},$ $R_S = 50 \Omega$	V <sub>O</sub> = 1.5 V,	25°C Full range	65 60	83		65 60	83		dB
				_				$\vdash$			
ksvr	Supply voltage rejection ratio	$V_{DD} = 2.7 \text{ V to 8 V},$ No load	$V_{IC} = V_{DD}/2$	25°C Full range	80 80	95		80 80	95		dB
	(ΔV <sub>DD</sub> /ΔV <sub>IO</sub> )			25°C	00	11	25	- 00	11	2F	
IDD	Supply current	V <sub>O</sub> = 1.5 V,	No load			11			11	25 30	μΑ
				Full range			30			30	

<sup>†</sup> Full range for the TLV2711C is 0°C to 70°C. Full range for the TLV2711I is – 40°C to 85°C.



<sup>‡</sup>Referenced to 1.5 V

NOTE 4: Typical values are based on the input offset voltage shift observed through 500 hours of operating life test at  $T_A = 150^{\circ}C$  extrapolated to  $T_A = 25^{\circ}C$  using the Arrhenius equation and assuming an activation energy of 0.96 eV.

## TLV2711, TLV2711Y Advanced LinCMOS™ RAIL-TO-RAIL MICROPOWER SINGLE OPERATIONAL AMPLIFIERS

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# operating characteristics at specified free-air temperature, $V_{DD} = 3 V$ (unless otherwise noted)

	PARAMETER	TEST COND	ITIONS	<b>+</b> +	Т	LV27110	С	1	LV2711	I	UNIT	
	PARAWETER	TEST COND	ITIONS	T <sub>A</sub> †	MIN	TYP	MAX	MIN	TYP	MAX	UNIT	
		V- 44V+040V	D. 10 kgt	25°C	0.01	0.025		0.01	0.025			
SR	Slew rate at unity gain	$V_{O} = 1.1 \text{ V to } 1.9 \text{ V},  R_{L} = 10 \text{ k}\Omega^{\ddagger}, \\ C_{L} = 100 \text{ pF}^{\ddagger}$		Full range	0.005			0.005			V/μs	
Vn	Equivalent input noise	f = 10 Hz		25°C		80			80		nV/√ <del>Hz</del>	
	voltage	f = 1 kHz		25°C		22			22		nv/√Hz	
V	Peak-to-peak equivalent input noise voltage	f = 0.1 Hz to 1 Hz		25°C		660			660		nV	
V <sub>N(PP)</sub>		f = 0.1 Hz to 10 Hz		25°C		880			880			
In	Equivalent input noise current			25°C		0.6			0.6		fA/√ <del>Hz</del>	
	Gain-bandwidth product	f = 10  kHz, $C_L = 100 \text{ pF}^{\ddagger}$	$R_L = 10 \text{ k}\Omega^{\ddagger}$ ,	25°C		56			56		kHz	
ВОМ	Maximum output-swing bandwidth	$V_{O(PP)} = 1 \text{ V},$ $R_{L} = 10 \text{ k}\Omega^{\ddagger},$	$A_V = 1,$ $C_L = 100 \text{ pF}^{\ddagger}$	25°C		7			7		kHz	
φm	Phase margin at unity gain	$R_L = 10 \text{ k}\Omega^{\ddagger}$ ,	C <sub>L</sub> = 100 pF‡	25°C		56°			56°	·		
	Gain margin			25°C		20			20		dB	

<sup>†</sup> Full range is –40°C to 85°C.

<sup>‡</sup>Referenced to 1.5 V

# electrical characteristics at specified free-air temperature, $V_{DD} = 5 \text{ V}$ (unless otherwise noted)

	PARAMETER	TEST CONDITIONS		T. †	Т	LV27110	С	٦	LV2711	I	UNIT
	PARAMETER	TEST COND	ITIONS	T <sub>A</sub> †	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
V <sub>IO</sub>	Input offset voltage					0.45	3		0.45	3	mV
αΛΙΟ	Temperature coefficient of input offset voltage			Full range		0.5			0.5		μV/°C
	Input offset voltage long-term drift (see Note 4)	$V_{DD\pm} = \pm 2.5 \text{ V},$ $V_{O} = 0,$	$V_{IC} = 0$ , R <sub>S</sub> = 50 $\Omega$	25°C		0.003			0.003		μV/mo
IIO	Input offset current			25°C		0.5	60		0.5	60	pА
10	Input onset ourrent	]		Full range			150			150	p/ t
IIB	Input bias current			25°C		1	60		1	60	pА
- 'וס	Input blub duriont			Full range			150			150	P/\
\/	Common-mode input	  V <sub>IO</sub>   ≤5 mV	Do 50.0	25°C	0 to 4	-0.3 to 4.2		0 to 4	-0.3 to 4.2		V
VICR	voltage range		$R_S = 50 \Omega$	Full range	0 to 3.5			0 to 3.5			V
		I <sub>OH</sub> = -100 μA		25°C		4.95			4.95		
Vон	High-level output voltage			25°C		4.875			4.875		V
011	voltage	I <sub>OH</sub> = -250 μA		Full range	4.6			4.6			
		V <sub>IC</sub> = 2.5 V,	I <sub>OL</sub> = 50 μA	25°C		12			12		
$V_{OL}$	Low-level output voltage	V <sub>IC</sub> = 2.5 V,	500 4	25°C		120			120		mV
			$I_{OL} = 500 \mu\text{A}$	Full range			500			500	
	Large-signal differential	V <sub>IC</sub> = 2.5 V, V <sub>O</sub> = 1 V to 4 V	p 401 of	25°C	6	12		6	12		
$A_{VD}$			$R_L = 10 \text{ k}\Omega^{\ddagger}$	Full range	3			3			V/mV
	voltage amplification	10-1164	$R_L = 1 M\Omega^{\ddagger}$	25°C		800			800		
<sup>r</sup> i(d)	Differential input resistance		•	25°C		1012			1012		Ω
ri(c)	Common-mode input resistance			25°C		1012			1012		Ω
Ci(c)	Common-mode input capacitance	f = 10 kHz,		25°C		5			5		pF
z <sub>O</sub>	Closed-loop output impedance	f = 7 kHz,	A <sub>V</sub> = 1	25°C		200			200		Ω
CMRR	Common-mode	$V_{IC} = 0 \text{ to } 2.7 \text{ V},$	V <sub>O</sub> = 2.5 V,	25°C	70	83		70	83		dB
CIVINK	rejection ratio	$R_S = 50 \Omega$		Full range	70			70			uБ
ksvr	Supply voltage rejection ratio	$V_{DD} = 4.4 \text{ V to 8 V},$ No load	$V_{IC} = V_{DD}/2$	25°C	80	95		80	95		dB
	(ΔV <sub>DD</sub> /ΔV <sub>IO</sub> )	110 1000		Full range	80			80			
I <sub>DD</sub>	Supply current	V <sub>O</sub> = 2.5 V,	No load	25°C		13	25	<u> </u>	13	25	μΑ
-טט				Full range			30			30	,

<sup>†</sup> Full range for the TLV2711C is 0°C to 70°C. Full range for the TLV2711I is – 40°C to 85°C.

NOTE 5: Typical values are based on the input offset voltage shift observed through 500 hours of operating life test at  $T_A = 150$ °C extrapolated to  $T_A = 25$ °C using the Arrhenius equation and assuming an activation energy of 0.96 eV.



<sup>‡</sup>Referenced to 1.5 V

# TLV2711, TLV2711Y Advanced LinCMOS™ RAIL-TO-RAIL MICROPOWER SINGLE OPERATIONAL AMPLIFIERS

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# operating characteristics at specified free-air temperature, $V_{DD} = 5 \text{ V}$ (unless otherwise noted)

	PARAMETER	TEST COND	ITIONS	<b>+</b> +	Т	LV27110	С	Т	LV2711	I	UNIT	
	PARAWETER	TEST COND	ITIONS	T <sub>A</sub> †	MIN	TYP	MAX	MIN	TYP	MAX	UNIT	
	Slew rate at unity gain	Va. 45 V to 25 V . D.		D. 10 kgt	25°C	0.01	0.025		0.01	0.025		
SR		$V_{O} = 1.5 \text{ V to } 3.5 \text{ V},  R_{L} = 10 \text{ k}\Omega^{\ddagger}, \\ C_{L} = 100 \text{ pF}^{\ddagger}$		Full range	0.005			0.005			V/μs	
V	Equivalent input noise	f = 10 Hz		25°C		72			72		->///	
Vn	voltage	f = 1 kHz		25°C		21			21		nV/√Hz	
V	Peak-to-peak equivalent input noise voltage	f = 0.1 Hz to 1 Hz		25°C		600			600		nV	
V <sub>N(PP)</sub>		f = 0.1 Hz to 10 Hz		25°C		800			800			
In	Equivalent input noise current			25°C		0.6			0.6		fA/√ <del>Hz</del>	
	Gain-bandwidth product	f = 10  kHz, $C_L = 100 \text{ pF}^{\ddagger}$	$R_L = 10 \text{ k}\Omega^{\ddagger}$ ,	25°C		65			65		kHz	
ВОМ	Maximum output-swing bandwidth	$V_{O(PP)} = 2 V,$ $R_{L} = 10 \text{ k}\Omega^{\ddagger},$	$A_V = 1,$ $C_L = 100 \text{ pF}^{\ddagger}$	25°C		7			7		kHz	
φm	Phase margin at unity gain	R <sub>L</sub> = 10 kΩ <sup>‡</sup> ,	C <sub>L</sub> = 100 pF‡	25°C		60°			60°	·		
	Gain margin			25°C		22			22		dB	

<sup>†</sup>Full range is -40°C to 85°C.

# electrical characteristics at $V_{DD}$ = 3 V, $T_A$ = 25°C (unless otherwise noted)

	DADAMETED	TEC	T CONDITIONS		T	LV2711Y	′		
	PARAMETER	163	ST CONDITIONS		MIN	TYP	MAX	UNIT	
۷IO	Input offset voltage					0.47		mV	
lio	Input offset current	$V_{DD\pm} = \pm 1.5 \text{ V},$ $R_S = 50 \Omega$	$V_O = 0$ ,	$V_{IC} = 0$ ,		0.5		рΑ	
I <sub>IB</sub>	Input bias current	115 - 00 22				1		pА	
VICR	Common-mode input voltage range	V <sub>IO</sub>   ≤5 mV,	$R_S = 50 \Omega$			-0.3 to 2.2		V	
V	High level output voltage	High-level output voltage			2.94				
VOH	High-level output voltage	I <sub>OH</sub> = -200 μA				2.85		V	
V/01	Low lovel output voltage	V <sub>IC</sub> = 0,	I <sub>OL</sub> = 50 μA			15		mV	
VOL	Low-level output voltage	V <sub>IC</sub> = 0,	I <sub>OL</sub> = 500 μA			150		1117	
Δ	Large-signal differential	V 4.5.V		$R_L = 10 \text{ k}\Omega^{\dagger}$		7		V/mV	
AVD	voltage amplification	V <sub>IC</sub> = 1.5 V,	$V_O = 1 V \text{ to } 2 V$	$R_L = 1 M\Omega^{\dagger}$		600		V/IIIV	
r <sub>i(d)</sub>	Differential input resistance					1012		Ω	
r <sub>i(c)</sub>	Common-mode input resistance					1012		Ω	
<sup>C</sup> i(c)	Common-mode input capacitance	f = 10 kHz				5		pF	
z <sub>o</sub>	Closed-loop output impedance	f = 7 kHz,	A <sub>V</sub> = 1			200		Ω	
CMRR	Common-mode rejection ratio	$V_{IC} = 0 \text{ to } 1.7 \text{ V},$	V <sub>O</sub> = 1.5 V,	R <sub>S</sub> = 50 Ω		83		dB	
kSVR	Supply voltage rejection ratio (ΔV <sub>DD</sub> /ΔV <sub>IO</sub> )	V <sub>DD</sub> = 2.7 V to 8 V,	$V_{IC} = V_{DD}/2,$	No load		95		dB	
$I_{DD}$	Supply current	V <sub>O</sub> = 1.5 V,	No load	·		11		μΑ	

<sup>†</sup> Referenced to 1.5 V



<sup>‡</sup>Referenced to 1.5 V

# electrical characteristics at $V_{DD}$ = 5 V, $T_A$ = 25°C (unless otherwise noted)

DADAMETED		756	CT CONDITIONS		TI	<i>'</i>		
	PARAMETER	l les	ST CONDITIONS		MIN	TYP	MAX	UNIT
VIO	Input offset voltage					0.45		mV
I <sub>IO</sub>	Input offset current	$V_{DD} \pm = \pm 2.5 \text{ V},$ $R_{S} = 50 \Omega$	$V_{IC} = 0$ ,	$V_O = 0$ ,		0.5		рА
I <sub>IB</sub>	Input bias current	11/5 = 30 22				1		рА
VICR	Common-mode input voltage range	V <sub>IO</sub>   ≤5 mV,	R <sub>S</sub> = 50 Ω			-0.3 to 4.2		V
\/-··	High level output voltage	I <sub>OH</sub> = -100 μA				4.95		V
VOH	High-level output voltage	$I_{OH} = -250 \mu\text{A}$				4.875		V
\/-·	Low lovel output voltage	V <sub>IC</sub> = 2.5 V,	I <sub>OL</sub> = 50 μA			12		mV
VOL	Low-level output voltage	V <sub>IC</sub> = 2.5 V,	I <sub>OL</sub> = 500 μA			120		IIIV
_	Large-signal differential	V 05.V		$R_L = 10 \text{ k}\Omega^{\dagger}$		12		\//\/
AVD	voltage amplification	$V_{IC} = 2.5 \text{ V},$	$V_O = 1 V \text{ to } 4 V$	$R_L = 1 M\Omega^{\dagger}$	800			V/mV
r <sub>i(d)</sub>	Differential input resistance			•		1012		Ω
r <sub>i(c)</sub>	Common-mode input resistance					1012		Ω
<sup>C</sup> i(c)	Common-mode input capacitance	f = 10 kHz				5		pF
z <sub>o</sub>	Closed-loop output impedance	f = 7 kHz,	A <sub>V</sub> = 1			200		Ω
CMRR	Common-mode rejection ratio	$V_{IC} = 0 \text{ to } 2.7 \text{ V},$	V <sub>O</sub> = 2.5 V,	$R_S = 50 \Omega$		83		dB
ksvr	Supply voltage rejection ratio (ΔV <sub>DD</sub> /ΔV <sub>IO</sub> )	V <sub>DD</sub> = 4.4 V to 8 V,	$V_{IC} = V_{DD}/2,$	No load		95		dB
I <sub>DD</sub>	Supply current	V <sub>O</sub> = 2.5 V,	No load			13		μА

<sup>†</sup>Referenced to 1.5 V

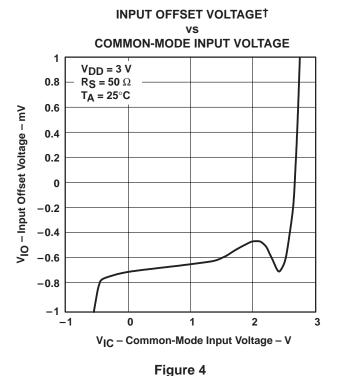
### **Table of Graphs**

			FIGURE
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I <sub>IB</sub> /I <sub>IO</sub>	Input bias and input offset currents	vs Free-air temperature	8
VI	Input voltage	vs Supply voltage vs Free-air temperature	9 10
Vон	High-level output voltage	vs High-level output current	11, 14
VOL	Low-level output voltage	vs Low-level output current	12, 13, 15
VO(PP)	Maximum peak-to-peak output voltage	vs Frequency	16
los	Short-circuit output current	vs Supply voltage vs Free-air temperature	17 18
٧o	Output voltage	vs Differential input voltage	19, 20
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z <sub>O</sub>	Output impedance	vs Frequency	26, 27
CMRR	Common-mode rejection ratio	vs Frequency vs Free-air temperature	28 29
ksvr	Supply-voltage rejection ratio	vs Frequency vs Free-air temperature	30, 31 32
I <sub>DD</sub>	Supply current	vs Supply voltage	33
SR	Slew rate	vs Load capacitance vs Free-air temperature	34 35
	Large-signal pulse response		36, 37, 38, 39
٧o	Inverting small-signal pulse response	vs Time	40, 41
	Small-signal pulse response		42, 43
V <sub>n</sub>	Equivalent input noise voltage	vs Frequency	44, 45
	Noise voltage (referred to input)	Over a 10-second period	46
THD + N	Total harmonic distortion plus noise	vs Frequency	47
	Gain-bandwidth product	vs Free-air temperature vs Supply voltage	48 49
φm	Phase margin	vs Frequency vs Load capacitance	23, 24 50
	Gain margin	vs Load capacitance	51
B <sub>1</sub>	Unity-gain bandwidth	vs Load capacitance	52



## **DISTRIBUTION OF TLV2711 INPUT OFFSET VOLTAGE** 546 Amplifiers From 1 Wafer Lot $V_{DD} = \pm 1.5 V$ T<sub>A</sub> = 25°C 20 Precentage of Amplifiers - % 15 10 5 -0.9 -0.5 -0.1 0.3 -1.3 0.7 1.1 1.5 VIO - Input Offset Voltage - mV

Figure 2



DISTRIBUTION OF TLV2711
INPUT OFFSET VOLTAGE

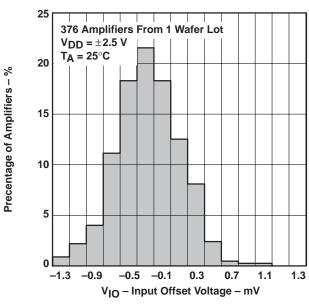


Figure 3

# INPUT OFFSET VOLTAGE† vs COMMON-MODE INPUT VOLTAGE

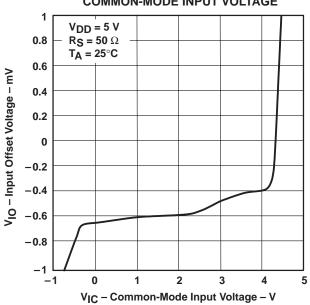


Figure 5

 $\dagger$  For all curves where  $V_{DD}$  = 5 V, all loads are referenced to 2.5 V. For all curves where  $V_{DD}$  = 3 V, all loads are referenced to 1.5 V.



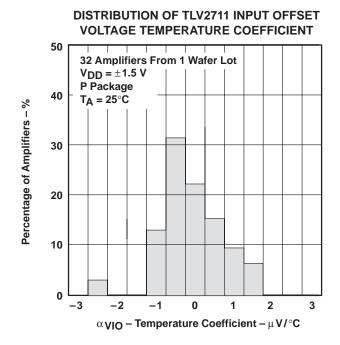
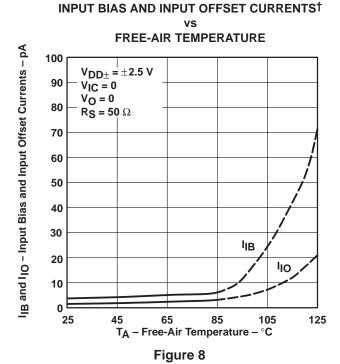


Figure 6



**DISTRIBUTION OF TLV2711 INPUT OFFSET VOLTAGE TEMPERATURE COEFFICIENT** 

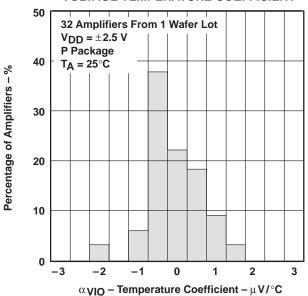
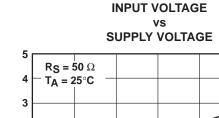


Figure 7



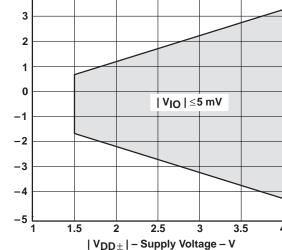


Figure 9

<sup>†</sup> Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



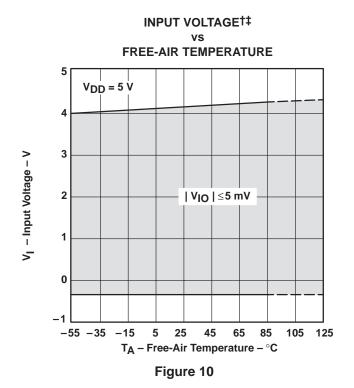
V<sub>I</sub> - Input Voltage - V

HIGH-LEVEL OUTPUT VOLTAGE†‡

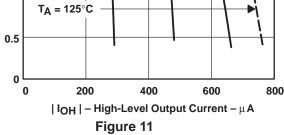
#### TYPICAL CHARACTERISTICS

1.5

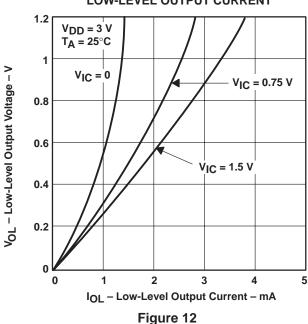
T<sub>A</sub> = 85°C



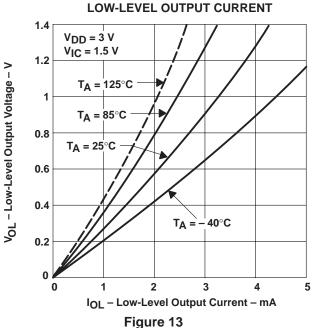
# **HIGH-LEVEL OUTPUT CURRENT** $V_{DD} = 3 V$ 2.5 VOH - High-Level Output Voltage - V $T_A = -40^{\circ}C$ 2 T<sub>A</sub> = 25°C







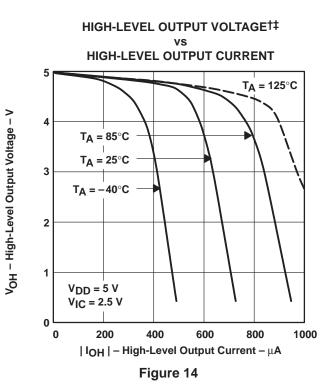
# LOW-LEVEL OUTPUT VOLTAGE†‡

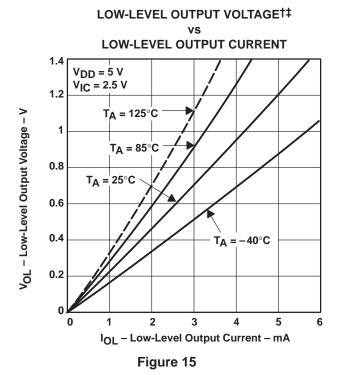


<sup>†</sup> Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

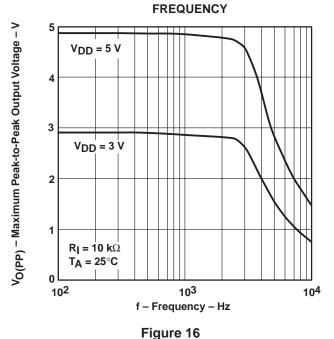
<sup>‡</sup> For all curves where V<sub>DD</sub> = 5 V, all loads are referenced to 2.5 V. For all curves where V<sub>DD</sub> = 3 V, all loads are referenced to 1.5 V.







# MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE‡



# SHORT-CIRCUIT OUTPUT CURRENT

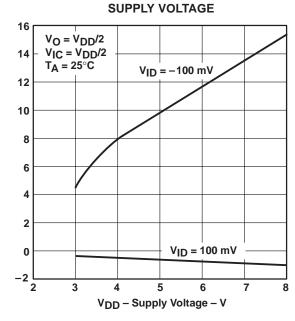


Figure 17

<sup>‡</sup> For all curves where V<sub>DD</sub> = 5 V, all loads are referenced to 2.5 V. For all curves where V<sub>DD</sub> = 3 V, all loads are referenced to 1.5 V.

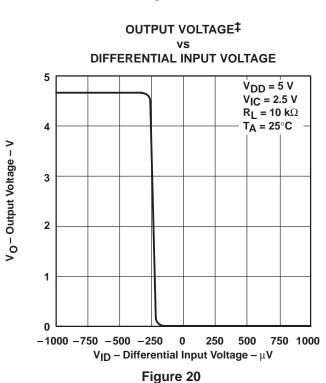


IOS - Short-Circuit Output Current - mA

<sup>†</sup> Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

### SHORT-CIRCUIT OUTPUT CURRENT†‡ FREE-AIR TEMPERATURE 14 V<sub>DD</sub> = 5 V V<sub>IC</sub> = 2.5 V IOS - Short-Circuit Output Current - mA 12 V<sub>O</sub> = 2.5 V 10 $V_{ID} = -100 \text{ mV}$ 8 2 $V_{ID} = 100 \text{ mV}$ 0 \_ -75 -50 25 75 100 125 TA - Free-Air Temperature - °C

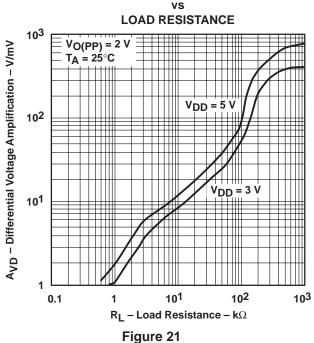
Figure 18



**OUTPUT VOLTAGE**‡ **DIFFERENTIAL INPUT VOLTAGE** 3  $V_{DD} = 3'V$  $R_I = 10 \text{ k}\Omega$  $V_{IC} = 1.5 \text{ V}$ 2.5  $T_A = 25^{\circ}C$ V<sub>O</sub> – Output Voltage – V 2 1.5 0.5 -1000 -750 -500 -250 0 250 500 750 1000 V<sub>ID</sub> - Differential Input Voltage - μV

# DIFFERENTIAL VOLTAGE AMPLIFICATION<sup>‡</sup>

Figure 19



<sup>†</sup>Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

<sup>‡</sup> For all curves where V<sub>DD</sub> = 5 V, all loads are referenced to 2.5 V. For all curves where V<sub>DD</sub> = 3 V, all loads are referenced to 1.5 V.



# LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE MARGIN†

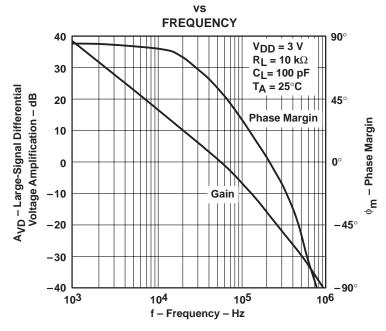


Figure 22

# LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE MARGIN<sup>†</sup>

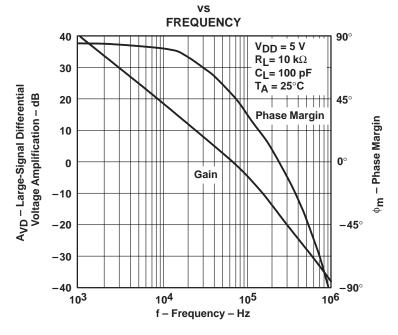
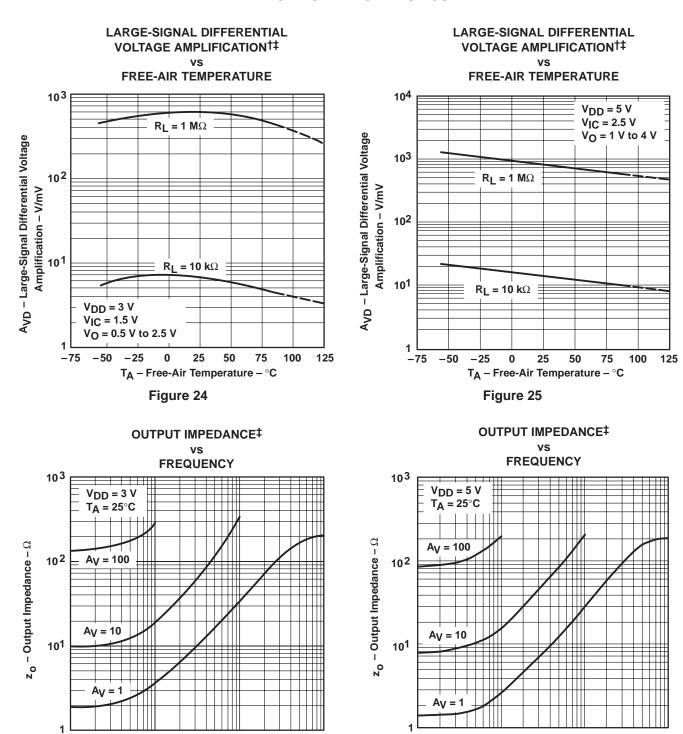


Figure 23

† For all curves where  $V_{DD} = 5 \text{ V}$ , all loads are referenced to 2.5 V. For all curves where  $V_{DD} = 3 \text{ V}$ , all loads are referenced to 1.5 V.





104

101

102

f- Frequency - Hz

Figure 26

103

<sup>‡</sup> For all curves where V<sub>DD</sub> = 5 V, all loads are referenced to 2.5 V. For all curves where V<sub>DD</sub> = 3 V, all loads are referenced to 1.5 V.



101

102

Figure 27

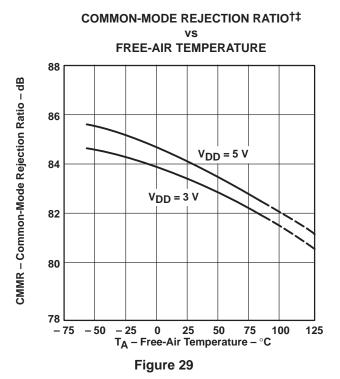
f- Frequency - Hz

103

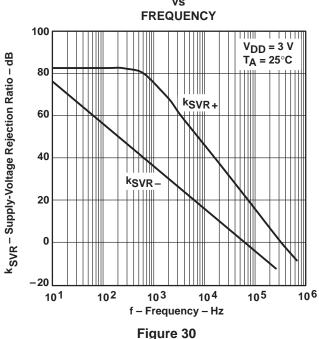
104

<sup>†</sup> Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

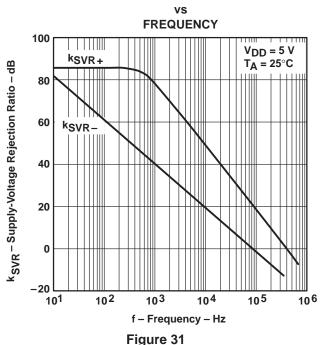
# **COMMON-MODE REJECTION RATIO**† **FREQUENCY** 100 T<sub>A</sub> = 25°C CMRR - Common-Mode Rejection Ratio - dB $V_{DD} = 5 V$ $V_0 = 2.5 \text{ V}$ 80 $V_{DD} = 3 V$ 60 $V_0 = 1.5 \text{ V}$ 40 20 101 102 104 f - Frequency - Hz Figure 28



## SUPPLY-VOLTAGE REJECTION RATIO† vs



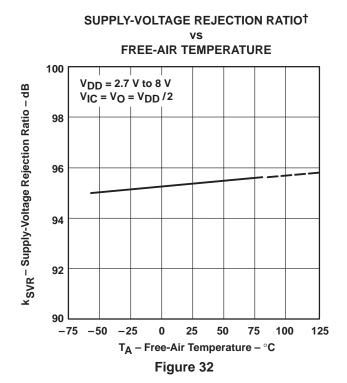
## SUPPLY-VOLTAGE REJECTION RATIO†

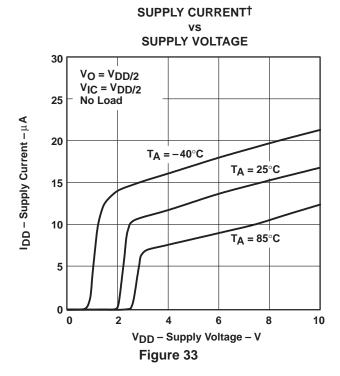


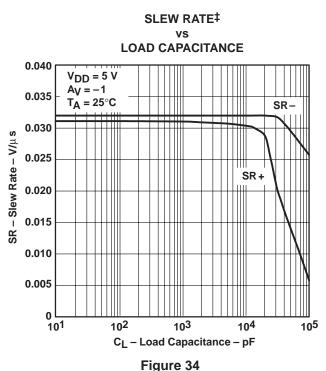
<sup>†</sup> For all curves where  $V_{DD} = 5$  V, all loads are referenced to 2.5 V. For all curves where  $V_{DD} = 3$  V, all loads are referenced to 1.5 V.

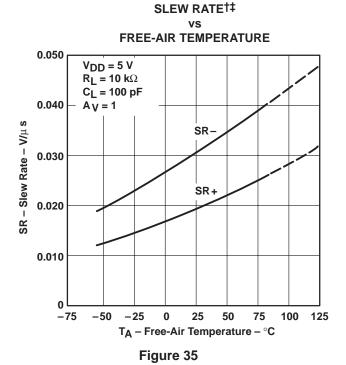
<sup>‡</sup> Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.











<sup>†</sup> Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

<sup>‡</sup> For all curves where V<sub>DD</sub> = 5 V, all loads are referenced to 2.5 V. For all curves where V<sub>DD</sub> = 3 V, all loads are referenced to 1.5 V.



# 



Figure 36

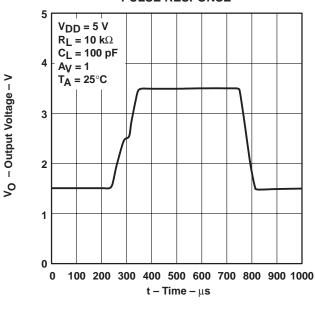
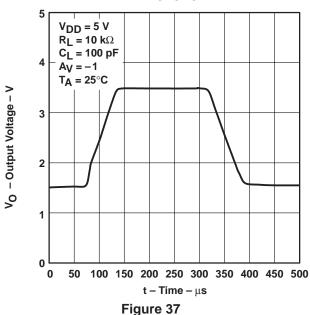
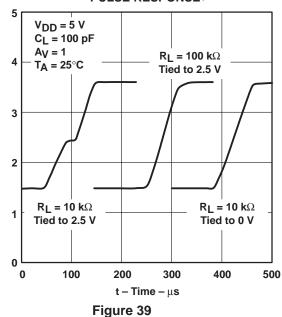


Figure 38

# INVERTING LARGE-SIGNAL PULSE RESPONSE†



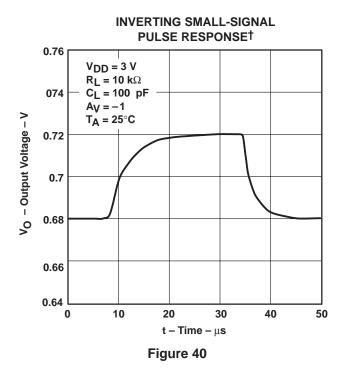
# VOLTAGE-FOLLOWER LARGE-SIGNAL PULSE RESPONSE<sup>†</sup>

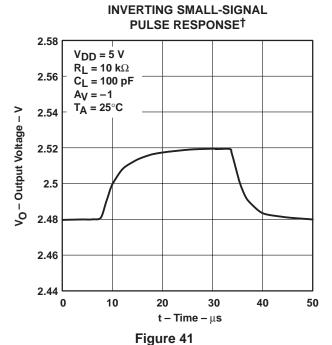


† For all curves where  $V_{DD} = 5 \text{ V}$ , all loads are referenced to 2.5 V. For all curves where  $V_{DD} = 3 \text{ V}$ , all loads are referenced to 1.5 V.



Vo - Output Voltage - V







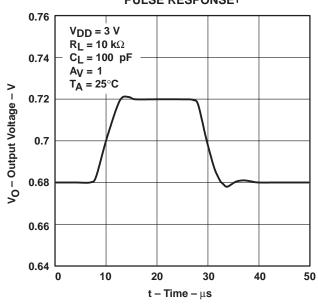


Figure 42

VOLTAGE-FOLLOWER SMALL-SIGNAL PULSE RESPONSE†

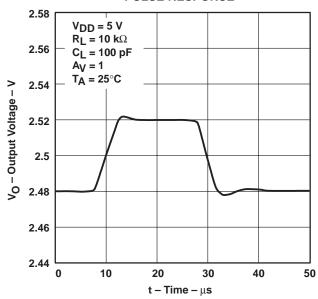
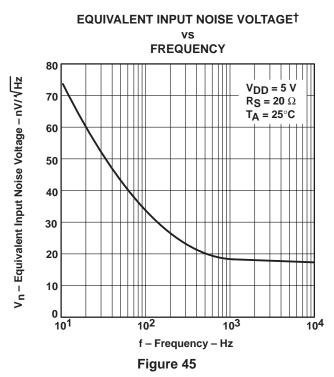


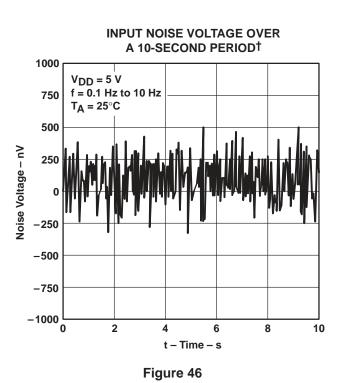
Figure 43

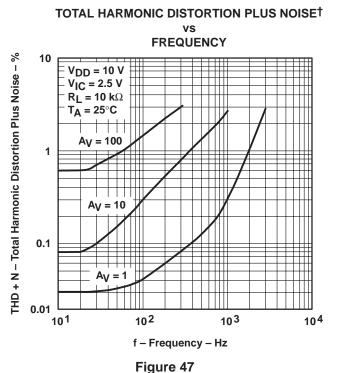
 $\dagger$  For all curves where  $V_{DD}$  = 5 V, all loads are referenced to 2.5 V. For all curves where  $V_{DD}$  = 3 V, all loads are referenced to 1.5 V.



## **EQUIVALENT INPUT NOISE VOLTAGE**<sup>†</sup> **FREQUENCY** 80 V<sub>n</sub> – Equivalent Input Noise Voltage – nV/ √Hz $V_{DD} = 3 V$ $R_S = 20 \Omega$ 70 T<sub>A</sub> = 25°C 60 50 40 30 20 10 101 102 103 104 f - Frequency - Hz Figure 44

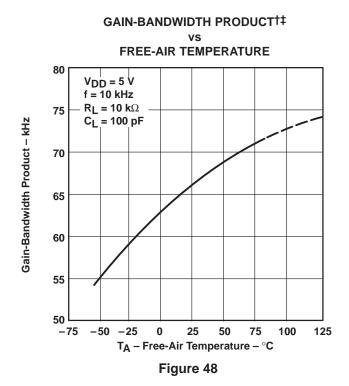


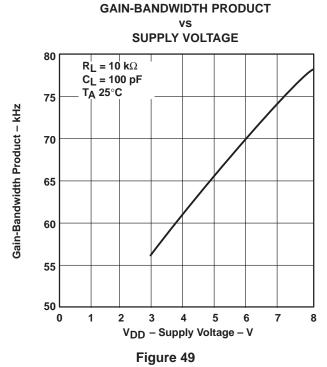


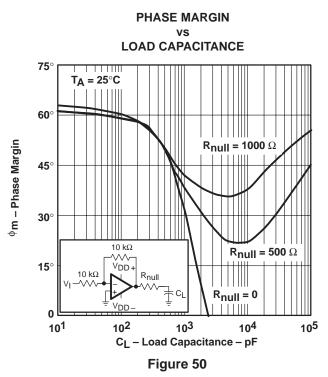


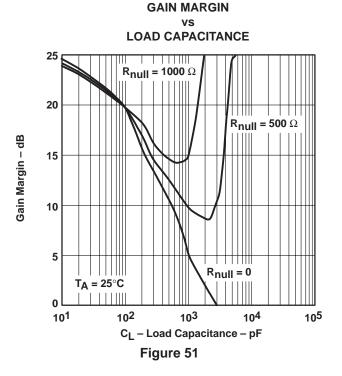
† For all curves where V<sub>DD</sub> = 5 V, all loads are referenced to 2.5 V. For all curves where V<sub>DD</sub> = 3 V, all loads are referenced to 1.5 V.











<sup>†</sup> Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

<sup>‡</sup> For all curves where V<sub>DD</sub> = 5 V, all loads are referenced to 2.5 V. For all curves where V<sub>DD</sub> = 3 V, all loads are referenced to 1.5 V.



# UNITY-GAIN BANDWIDTH vs

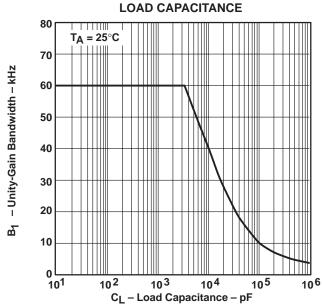


Figure 52

#### **APPLICATION INFORMATION**

#### driving large capacitive loads

The TLV2711 is designed to drive larger capacitive loads than most CMOS operational amplifiers. Figure 50 and Figure 51 illustrate its ability to drive loads up to 600 pF while maintaining good gain and phase margins  $(R_{null} = 0)$ .

A smaller series resistor ( $R_{null}$ ) at the output of the device (see Figure 53) improves the gain and phase margins when driving large capacitive loads. Figure 50 and Figure 51 show the effects of adding series resistances of 500  $\Omega$  and 1000  $\Omega$ . The addition of this series resistor has two effects: the first is that it adds a zero to the transfer function and the second is that it reduces the frequency of the pole associated with the output load in the transfer function.

The zero introduced to the transfer function is equal to the series resistance times the load capacitance. To calculate the improvement in phase margin, equation 1 can be used.

$$\Delta \phi_{\text{m1}} = \tan^{-1} \left( 2 \times \pi \times \text{UGBW} \times R_{\text{null}} \times C_{\text{L}} \right)$$
 (1)

Where:

 $\Delta \phi_{m1}$  = Improvement in phase margin

UGBW = Unity-gain bandwidth frequency

R<sub>null</sub> = Output series resistance

 $C_1$  = : Load capacitance



#### APPLICATION INFORMATION

#### driving large capacitive loads (continued)

The unity-gain bandwidth (UGBW) frequency decreases as the capacitive load increases (see Figure 52). To use equation 1, UGBW must be approximated from Figure 52.

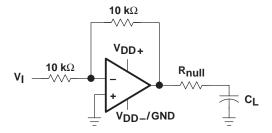


Figure 53. Series-Resistance Circuit

#### driving heavy dc loads

The TLV2711 is designed to provide better sinking and sourcing output currents than earlier CMOS rail-to-rail output devices. This device is specified to sink 500  $\mu$ A and source 250  $\mu$ A at V<sub>DD</sub> = 3 V and V<sub>DD</sub> = 5 V at a maximum quiescent I<sub>DD</sub> of 25  $\mu$ A. This provides a greater than 90% power efficiency.

When driving heavy dc loads, such as  $10 \text{ k}\Omega$ , the positive edge under slewing conditions can experience some distortion. This condition can be seen in Figure 38. This condition is affected by three factors.

- Where the load is referenced. When the load is referenced to either rail, this condition does not occur. The distortion occurs only when the output signal swings through the point where the load is referenced. Figure 39 illustrates two  $10-k\Omega$  load conditions. The first load condition shows the distortion seen for a  $10-k\Omega$  load tied to 2.5 V. The third load condition shows no distortion for a  $10-k\Omega$  load tied to 0 V.
- Load resistance. As the load resistance increases, the distortion seen on the output decreases. Figure 39 illustrates the difference seen on the output for a  $10-k\Omega$  load and a  $100-k\Omega$  load with both tied to 2.5 V.
- Input signal edge rate. Faster input edge rates for a step input result in more distortion than with slower input edge rates.



#### **APPLICATION INFORMATION**

#### macromodel information

Macromodel information provided was derived using Microsim  $Parts^{TM}$ , the model generation software used with Microsim  $PSpice^{TM}$ . The Boyle macromodel (see Note 6) and subcircuit in Figure 54 are generated using the TLV2711 typical electrical and operating characteristics at  $T_A = 25$ °C. Using this information, output simulations of the following key parameters can be generated to a tolerance of 20% (in most cases):

- Maximum positive output voltage swing
- Maximum negative output voltage swing
- Slew rate
- Quiescent power dissipation
- Input bias current
- Open-loop voltage amplification

- Unity-gain frequency
- Common-mode rejection ratio
- Phase margin
- DC output resistance
- AC output resistance
- Short-circuit output current limit

NOTE 6: G. R. Boyle, B. M. Cohn, D. O. Pederson, and J. E. Solomon, "Macromodeling of Integrated Circuit Operational Amplifiers", *IEEE Journal of Solid-State Circuits*, SC-9, 353 (1974).

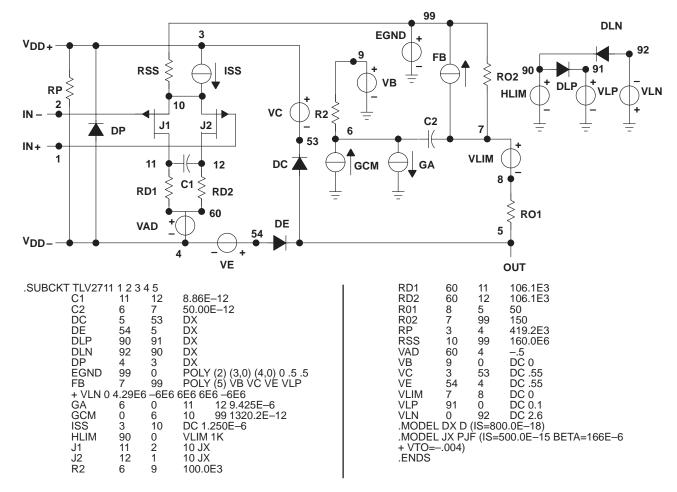


Figure 54. Boyle Macromodel and Subcircuit

PSpice and Parts are trademark of MicroSim Corporation.



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#### PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TLV2711CDBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	VAJC	Samples
TLV2711CDBVT	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM		VAJC	Samples
TLV2711IDBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VAJI	Samples
TLV2711IDBVT	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM		VAJI	Samples
TLV2711IDBVTG4	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM		VAJI	Samples

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.



### **PACKAGE OPTION ADDENDUM**

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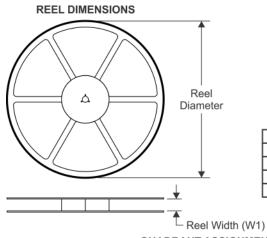
Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

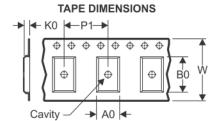
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

## PACKAGE MATERIALS INFORMATION

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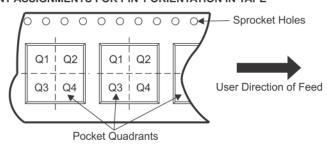
### TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV2711CDBVR	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
TLV2711CDBVT	SOT-23	DBV	5	250	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
TLV2711IDBVR	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
TLV2711IDBVT	SOT-23	DBV	5	250	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3

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\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV2711CDBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
TLV2711CDBVT	SOT-23	DBV	5	250	180.0	180.0	18.0
TLV2711IDBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
TLV2711IDBVT	SOT-23	DBV	5	250	180.0	180.0	18.0



SMALL OUTLINE TRANSISTOR



#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
  2. This drawing is subject to change without notice.
  3. Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
- 5. Support pin may differ or may not be present.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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